

MENU

SEARCH

INDEX

DETAIL

JAPANESE

BACK

NEXT

7 / 8

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 08-248626
 (43)Date of publication of application : 27.09.1996

(51)Int.Cl. G03F 7/004
 G03F 7/039
 H01L 21/027

(21)Application number : 07-074629

(22)Date of filing : 07.03.1995

(71)Applicant : SHIN ETSU CHEM CO LTD
 NIPPON TELEGR & TELEPH CORP <NTT>

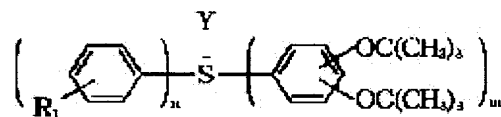
(72)Inventor : OSAWA YOICHI
 WATANABE SATOSHI
 ISHIHARA TOSHINOBU
 TANAKA HARUYORI
 KAWAI YOSHIO
 NAKAMURA JIRO

(54) CHEMICALLY SENSITIZED POSITIVE RESIST MATERIAL

(57)Abstract:

PURPOSE: To provide a chemically sensitized positive resist material which has a high sensitivity against high energy beam radiation such as far ultraviolet rays, electron beam, and X-rays, and by which pattern formation can be made by developing it with an alkali aqueous solution, so that it is suitable for fine working technique.

CONSTITUTION: A chemically sensitized positive resist material is that which includes a new sulfonium salt as shown by the formula. In the formula, R1 denotes a hydrogen atom, alkyl group, alkoxyl group or dialkylamino group, and Y denotes trisulfomethanesulfonate or p-toluensulfonate. The n is an integer of 0 to 2, m is an integer of 1 to 3, and n+m=3.



LEGAL STATUS

[Date of request for examination]

27.04.2000

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the
examiner's decision of rejection or application converted
registration]

[Date of final disposal for application]

[Patent number] 3399141

[Date of registration] 21.02.2003

[Number of appeal against examiner's decision of
rejection]

[Date of requesting appeal against examiner's decision of
rejection]

[Date of extinction of right]